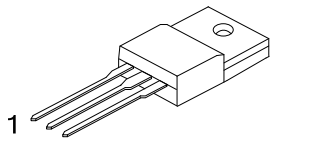
TGBR10S120C

Preliminary ***DIODE***

DUAL TRENCH MOS SCHOTTKY BARRIER RECTIFIER



TO-220F1

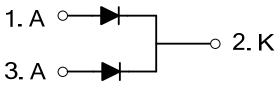
■ DESCRIPTION

The UTC **TGBR10S120C** is a dual trench mos schottky barrier rectifier, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed, etc.

■ FEATURES

*Super low forward voltage drop
* High switching speed

■ SYMBOL



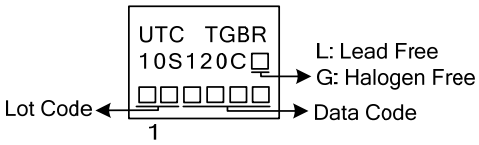
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
TGBR10S120CL-TF1-T	TGBR10S120CG-TF1-T	TO-220F1	A	K	A	Tube

Note: Pin Assignment: A: Anode K: Cathode

TGBR10S120CL-TF1-T (1)Packing Type	(1) T: Tube
(2)Package Type	(2) TF1: TO-220F1
(3)Green Package	(3) L: Lead Free, G: Halogen Free and Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.
For capacitance load, derate current by 20%.

PARAMETER		SYMBOL	RATINGS	UNIT
DC Blocking Voltage		V_{RM}	120	V
Working Peak Reverse Voltage		V_{RWM}	120	V
Peak Repetitive Reverse Voltage		V_{RRM}	120	V
Average Rectified Output Current Per Device	Per Leg	I_O	5	A
	Total		10	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load		I_{FSM}	100	A
Operating Junction Temperature		T_J	-65 ~ +150	°C
Storage Temperature		T_{STG}	-65 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS (PER LEG)

PARAMETER	SYMBOL	RATINGS	UNIT
Typical Thermal Resistance	θ_{JC}	4	°C/W

■ ELECTRICAL CHARACTERISTICS (PER LEG) (T_A =25°C unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage	$V_{(BR)R}$	I_R=0.50mA	120			V
Forward Voltage Drop	V_{FM}	I_F=5A, T_J=25°C			0.75	V
		I_F=5A, T_J=125°C			0.70	V
Leakage Current	I_{RM}	V_R=120V, T_J=25°C			100	μA
		V_R=120V, T_J=125°C			20	mA

Note: Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.